



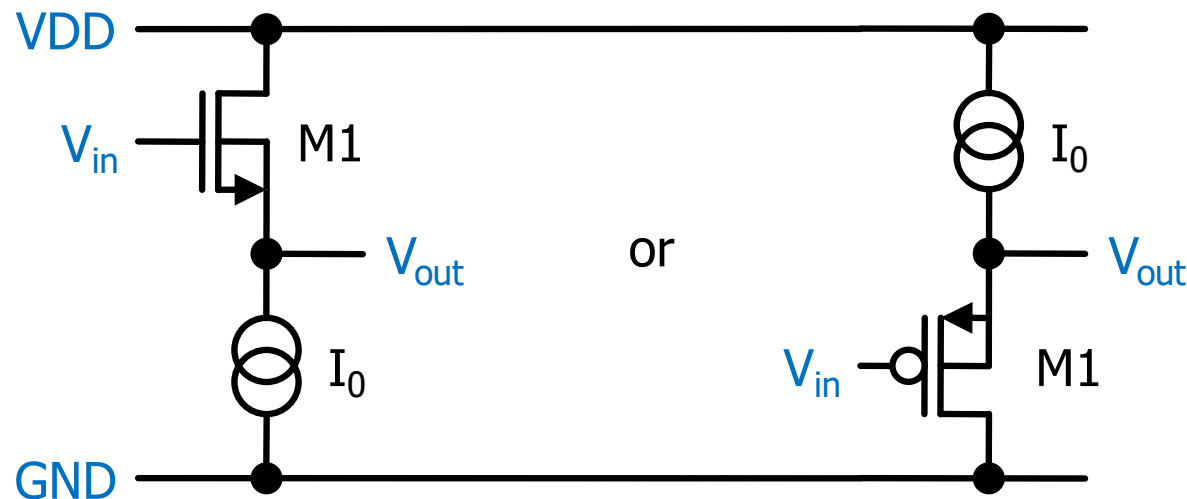
# The Source Follower



# The Source Follower (Common Drain Stage, SF)

- Current source  $I_0$  pulls a *constant* current through the MOS
- This fixes  $V_{GS}$  of M1 (to  $V_T + \text{Sqrt}(\dots)$ )
- Therefore,  $V_{in} - V_{out} = V_{GS}$  is *nearly* constant (see later)
- The small signal gain is close to 1

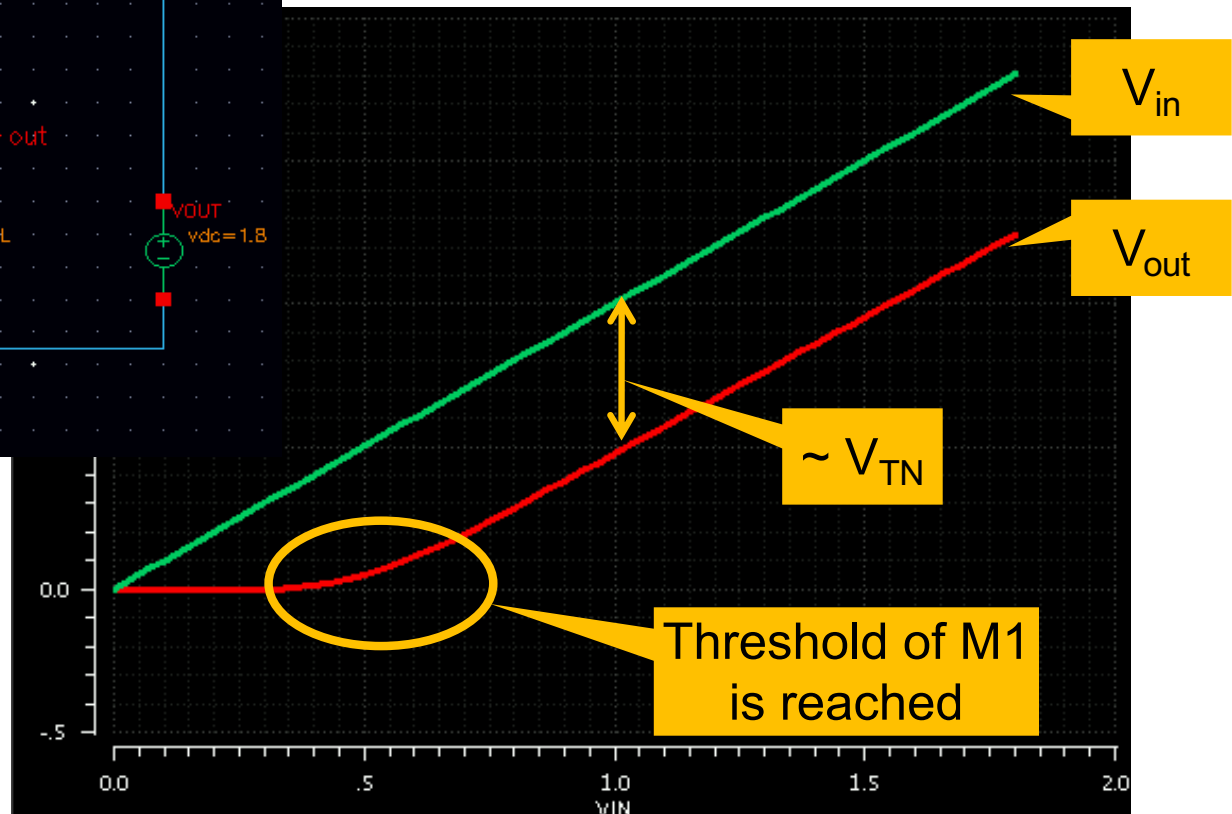
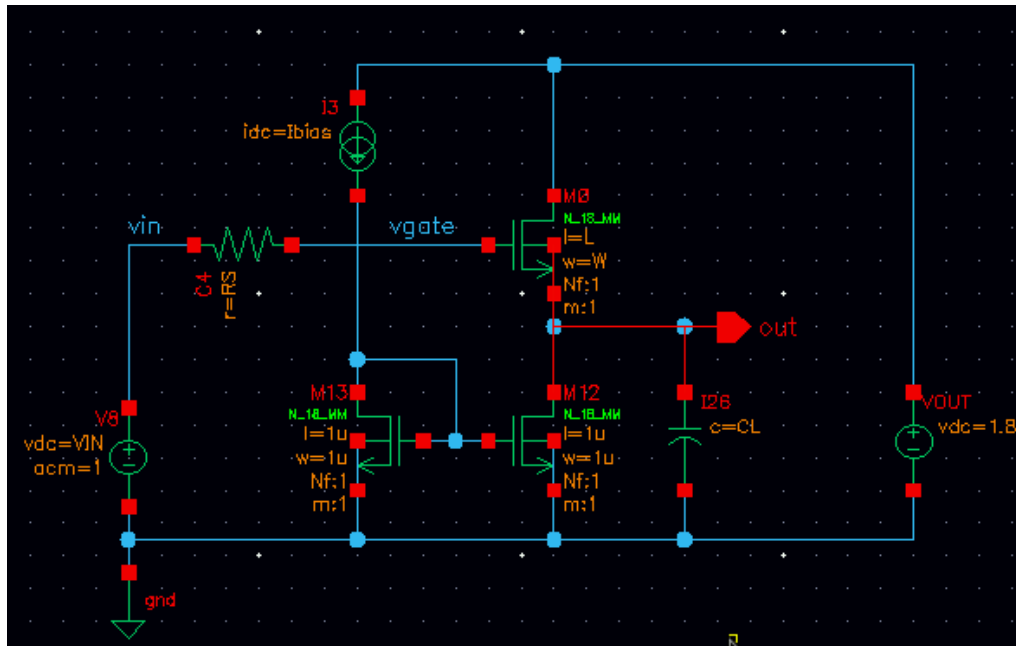
$$V_{out} \sim V_{in} - \text{constant} \rightarrow v_{out} \sim v_{in} \rightarrow g = v_{out}/v_{in} \sim 1$$





# Simulation

- NMOS Source Follower with NMOS current source:
  - Starts to work when  $V_{in} > V_{T,NMOS} + V_{DSat,Source}$

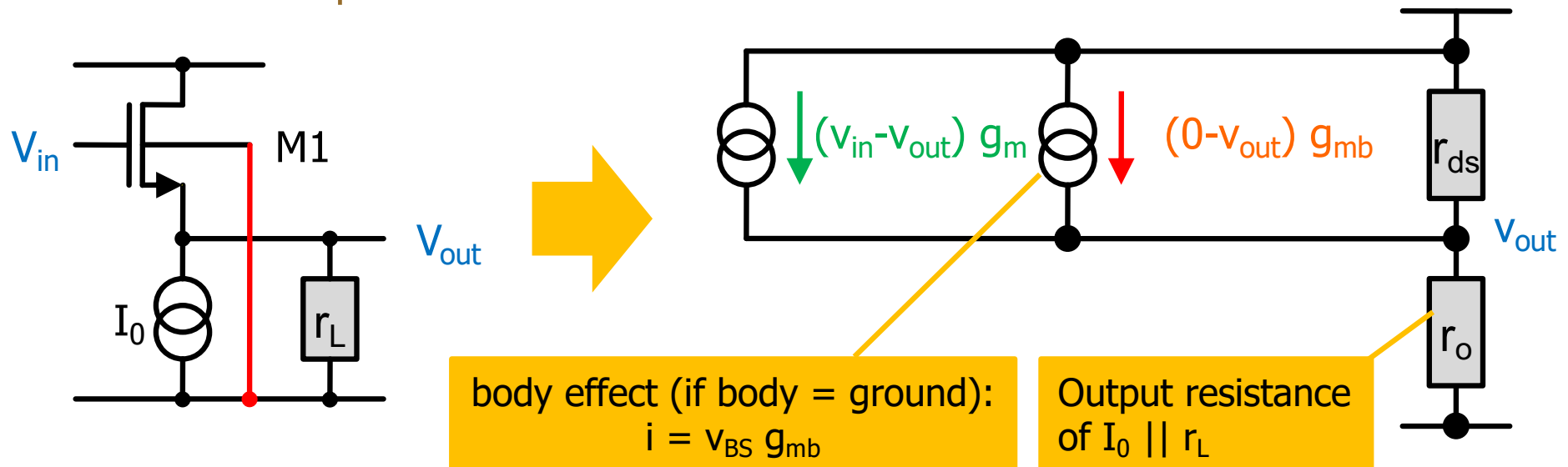




# Real Source Follower (Here *with* substrate effect)

■ In reality, we must consider

- $r_{ds}$  of M1
- the body effect of M1 (if  $V_B \neq V_S$ )
- the finite output resistance of  $I_0$
- a possible load resistor



$$(v_{in} - v_{out}) g_m + (0 - v_{out}) g_{mb} + \frac{(0 - v_{out})}{r_{ds}} = \frac{v_{out}}{r_o}$$



# Real Source Follower (Here *with* substrate effect)

## ▪ DC Gain:

$$\text{gain} = \frac{g_m}{g_{ds} + g_m + g_{mb} + g_o}$$

- With  $g_{ds} = 1 / r_{ds}$ ,  $g_o = 1/r_o + 1/R_L$
- Gain is *always*  $\leq 1$ .
  - With body effect (remember:  $g_{mb} = (n-1) g_m$ ),  $\text{gain} \sim 1/n \sim 0.7$ .  
Try to avoid body effect  $\rightarrow$  PMOS in well or triple well NMOS
  - A load resistance  $R_L$  ( $\rightarrow g_o$ ) lowers the gain.  
The SF cannot drive resistive loads well.
  - Output resistance of  $I_0$  can be improved by long MOS or cascode.
- In transient situations, the NMOS SF can *source* a large current but can *sink* only  $I_0$ .



# Source Follower with $g=1$ ?

- From  $g = \frac{g_m}{g_{ds} + g_i + g_m + g_{mb}}$  we see that we approach  $g=1$  with
  - $g_{mb} = 0 \rightarrow$  connect bulk an source of M1. This is often not possible for NMOS (bulk = substrate = ground)
  - $g_i = 0 \rightarrow$  Make a good current source:
    - long MOS
    - Cascode, ...
 This will lead to higher  $V_{DSat}$  so that SF works ,later‘
  - $g_{ds} = 0 \rightarrow$  Hard.
    - Longer MOS helps, but  $g_m$  suffers (ratio does not increase quickly, speed suffers)
    - Cascode not possible because we change source!

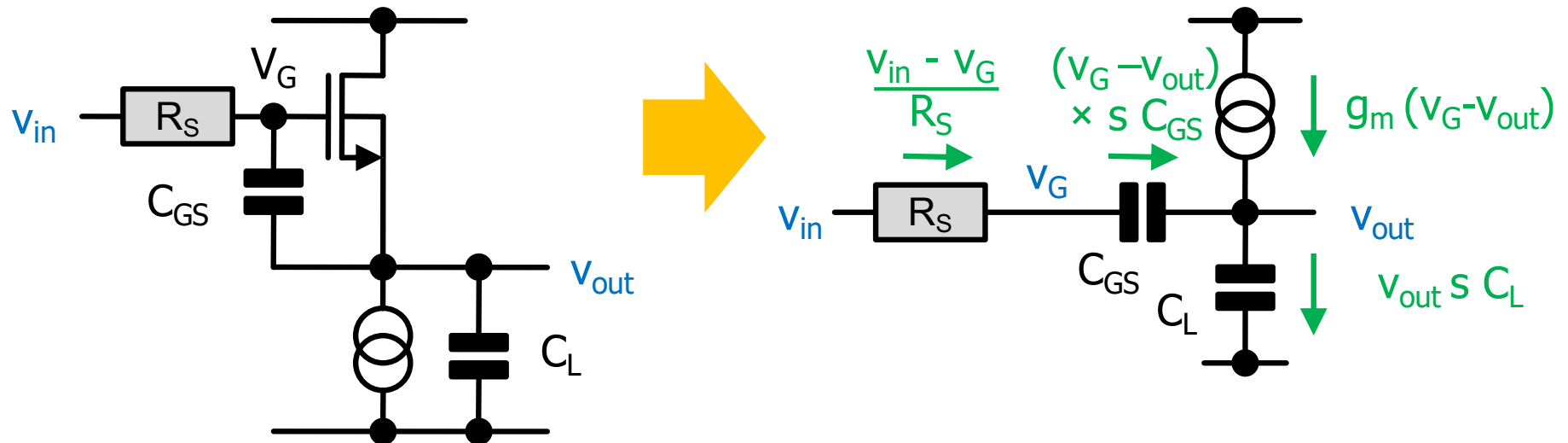


# Advanced: Source Follower with finite source imp.

For instance  
a gain stage

- Consider the case when the SF is driven by a 'high impedance' source (with output resistance  $R_S$ ):

- Take into account the Gate-Source cap.  $C_{GS}$  and output cap.  $C_L$
- We neglect output impedances and  $g_{mb}$  for simplicity...



- Solving the current equations at the two nodes  $V_G$  and  $V_{out}$  yields the transfer function  $V_{out}/V_{in}$ :

$$\frac{g_m + C_{gs} s}{g_m + s (C_{gs} + C_L + C_{gs} C_L R_S s)}$$



# Analysis

- This Transfer function has two poles (denom. 2<sup>nd</sup> order in s)

$$\frac{g_m + C_{gs} s}{g_m + s (C_{gs} + C_L + C_{gs} C_L R_S s)}$$

- The two poles are at  $-\frac{C_{gs} + C_L + \sqrt{(C_{gs} + C_L)^2 - 4 C_{gs} C_L g_m R_S}}{2 C_{gs} C_L R_S}$

- They become complex if the root is negative. This is at

$$R_S \rightarrow \frac{(C_{gs} + C_L)^2}{4 C_{gs} C_L g_m}$$

- There can be an *Overshoot* if  $R_S$  is *larger* than this value
- Worst case (smallest  $R_S$ ) is for  $C_{gs} = C_L$ .  
Then the limit is at  $R_S = 1/g_m$





# Analysis

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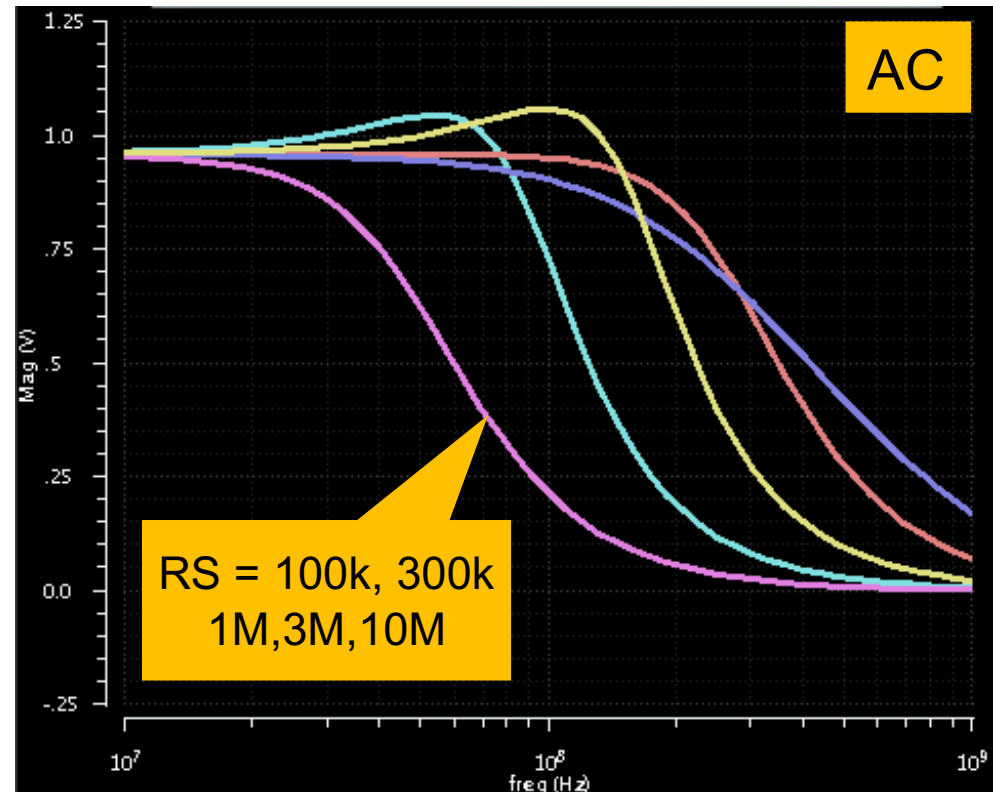
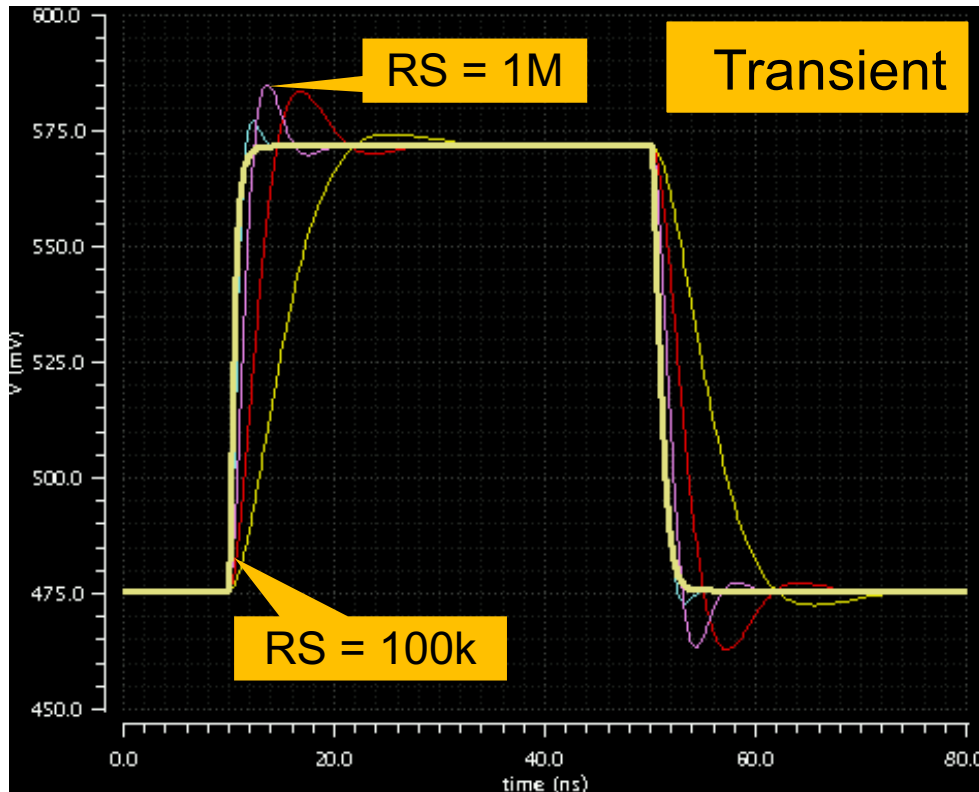
$$R_S \rightarrow \frac{(C_{gs} + C_L)^2}{4 C_{gs} C_L g_m}$$

- There can be an *Overshoot* if  $R_S$  is *larger* than this value



# Simulation

- 180nm Technology,  $W/L = 1\mu/0.18\mu$ ,  $C_L = 100\text{fF}$ ,  $I_{\text{bias}} = 10\mu\text{A}$

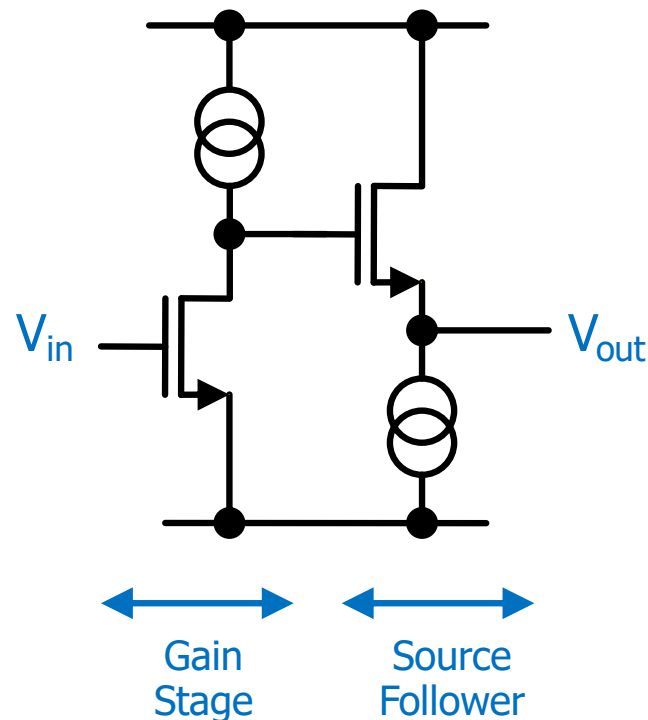


- Therefore remember:  
Source Followers driving capacitive loads are ***dangerous!***



# What for?

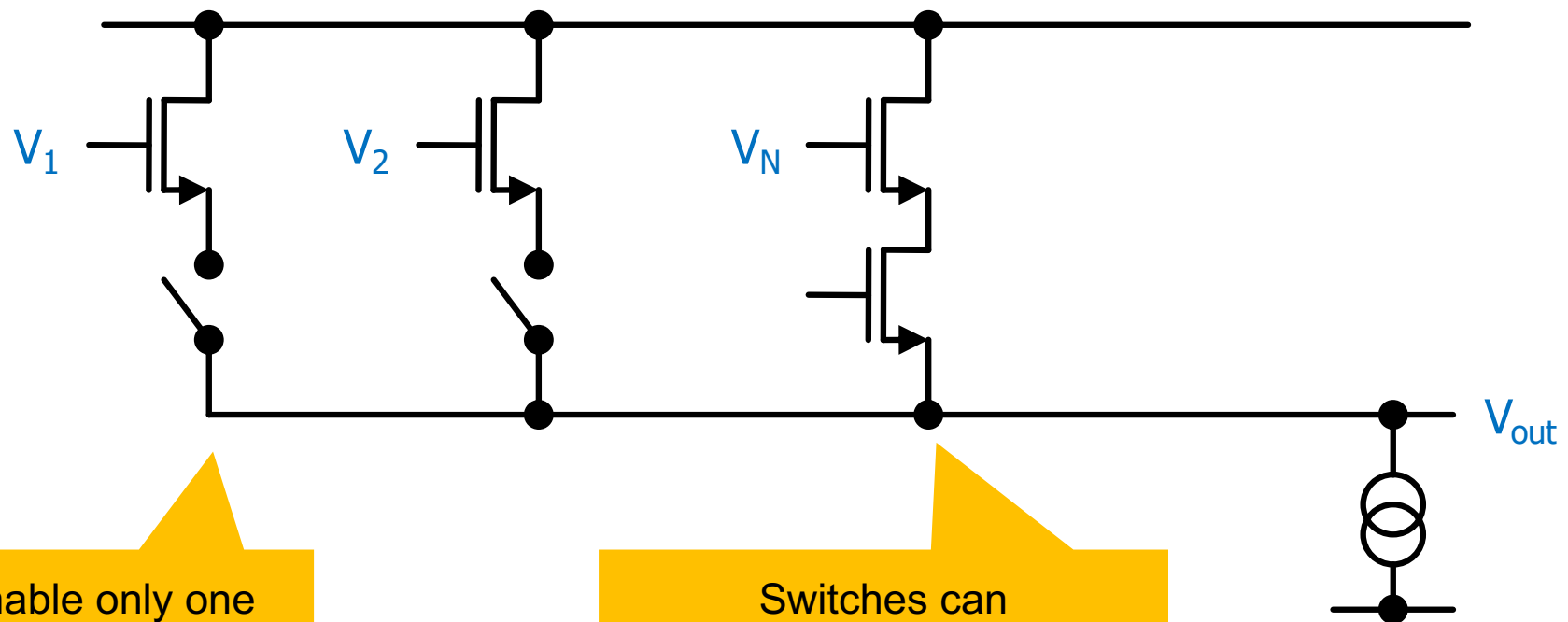
- The Source Follower has a low output impedance ( $1/g_m$ )
- It can 'drive' low-impedance (capacitive) loads
- Gain drops 'only a bit'
  - gain of a gain stage drops 'a lot' with resistive loads
- Often used in combination with a gain stage:





# Special Application

- SF be used to ,send' a voltage
- Multiple Source Followers can be combined:



Enable only one  
,channel' at a time

Switches can  
be NMOS (on output side)



# Advanced Followers



# The 'Flipped Voltage Follower' (FVF)

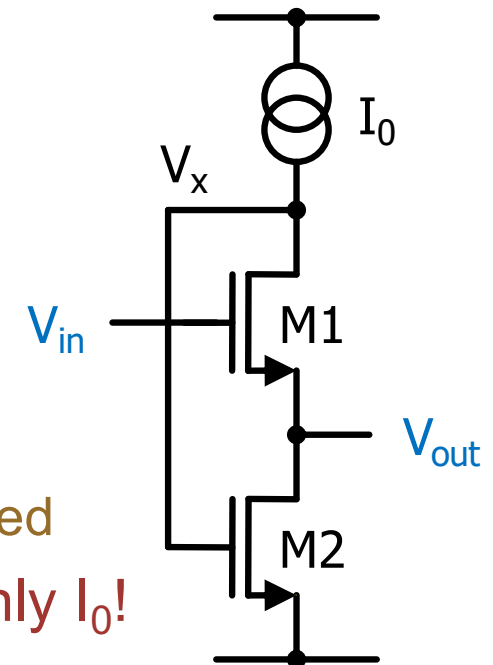
- A VERY clever and tricky circuit!
- $V_{out}$  'follows'  $V_{in}$  (as with normal SF), but
  - gain is much closer to 1, in particular for resistive load
  - Output impedance is much lower
- The current  $I_{M1}$  through M1 is always  $I_0$ , *independent* of load current  $\rightarrow V_{GS1}$  of M1 is constant  $\rightarrow g$  is closer to 1

- Regulation:

- Assume  $V_{out}$  raises
- $V_{GS1}$  drops
- $I_{M1}$  drops
- More current flows into node x than out of x
- $V_x = V_{GS2}$  rises
- $I_{M2}$  rises, pulling  $V_{out}$  low until  $V_{in} - V_{out}$  is restored

- FVF can *sink* a lot of current and *source* only  $I_0$ !

- Very clever!

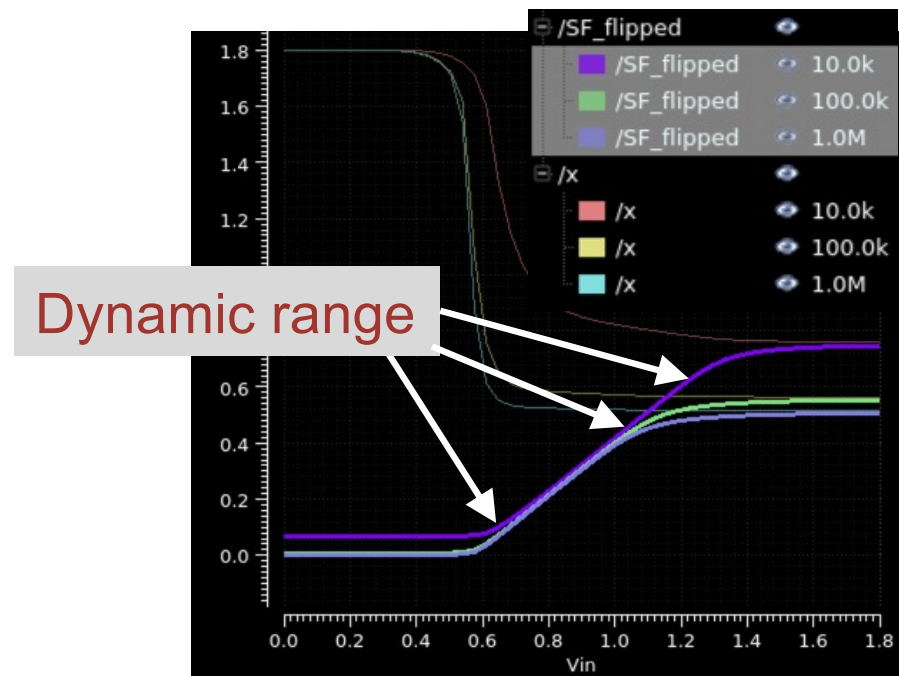
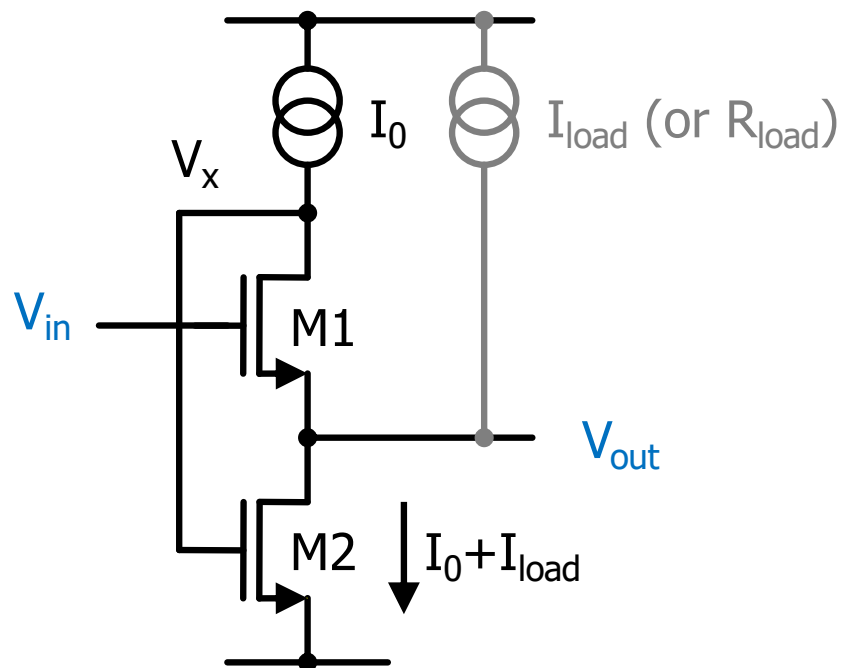




# Biassing Issue of the FVF

## Assuming no load current:

- $V_x = V_{GS2}$  is fixed by  $I_0$ . It is relatively 'low':  $V_{TN} + \sqrt{\dots}$
- When  $V_{in}$  becomes too positive, the drain voltage of M1 becomes too low. The circuit stops working.
- Input voltage range is *increased* with (positive!) load current  
Because more current flows in M2 and  $V_x$  rises!

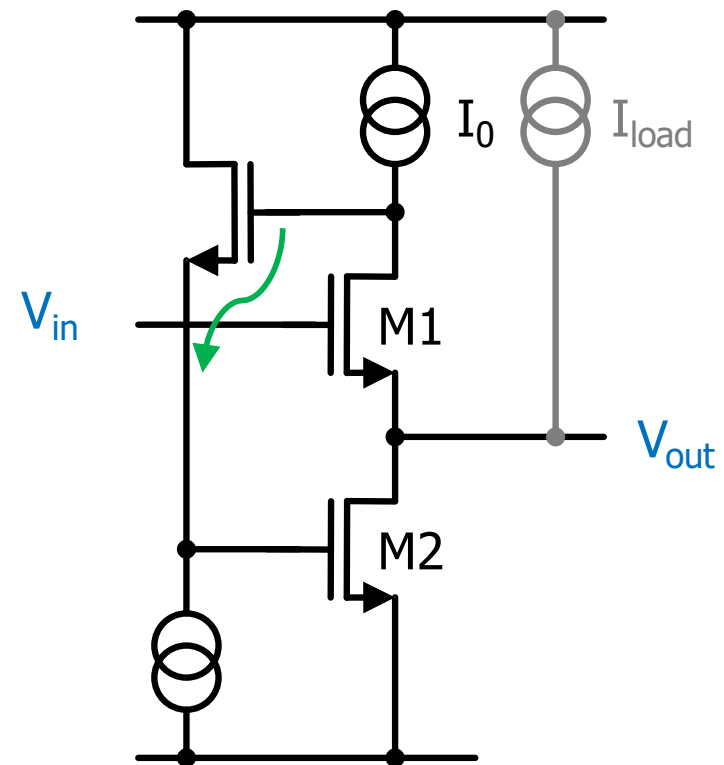
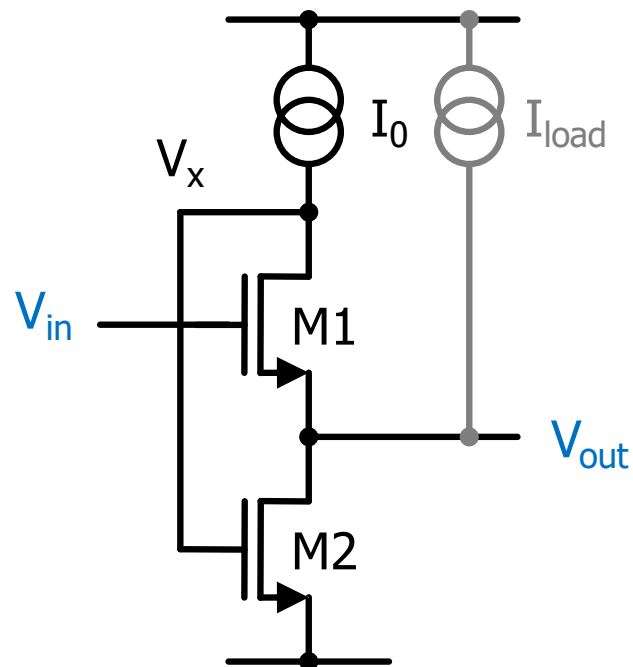


$I_0 = 10\mu A$ ,  $R_{load} = 10/100/1000 \text{ k}$



# Improvement – With Level Shifter

- The saturation issue can be reduced by shifting voltage  $x$  with a 'normal' source follower:

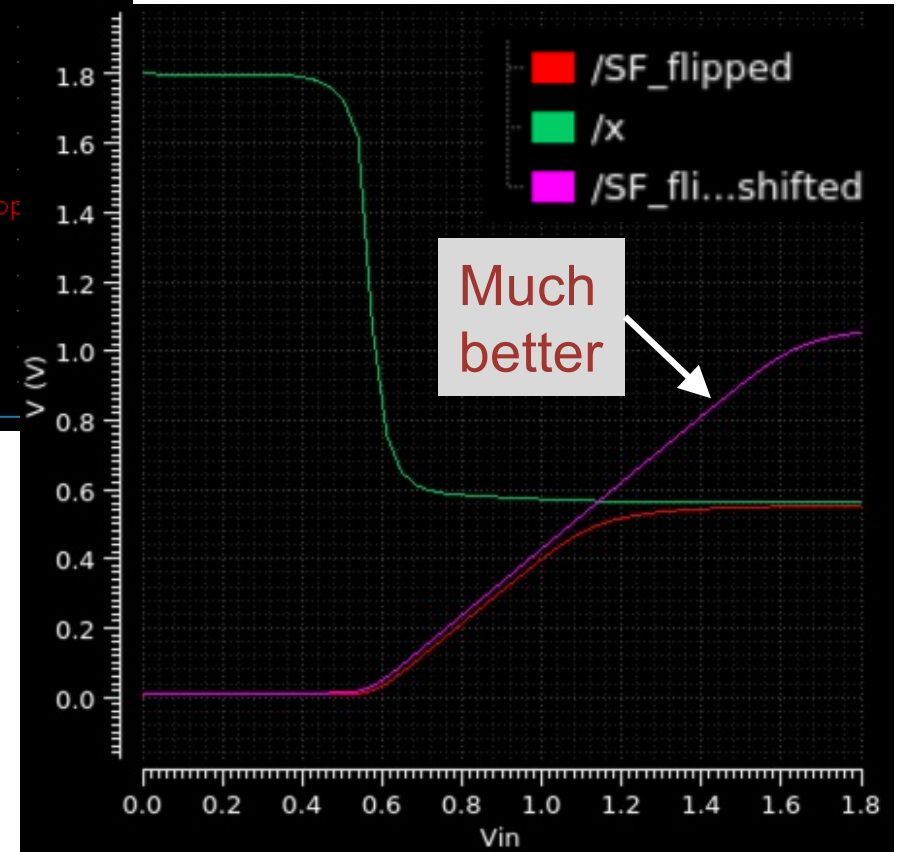
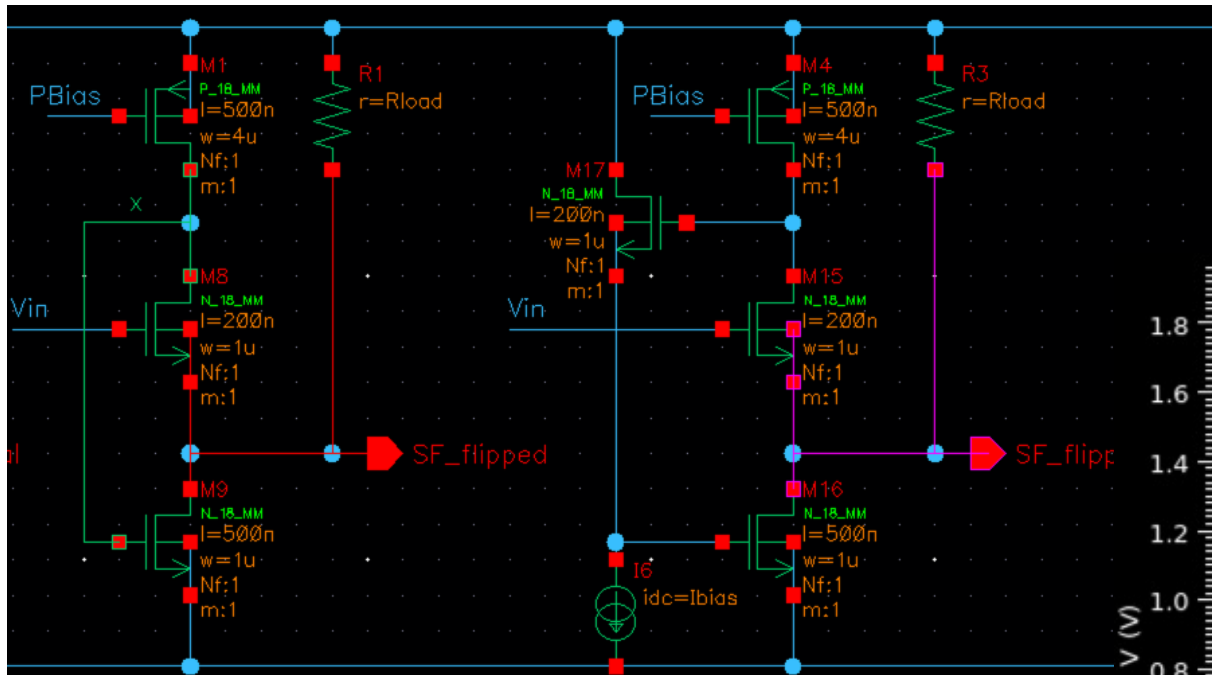


- If we have an MOS with high threshold, this helps for M2!





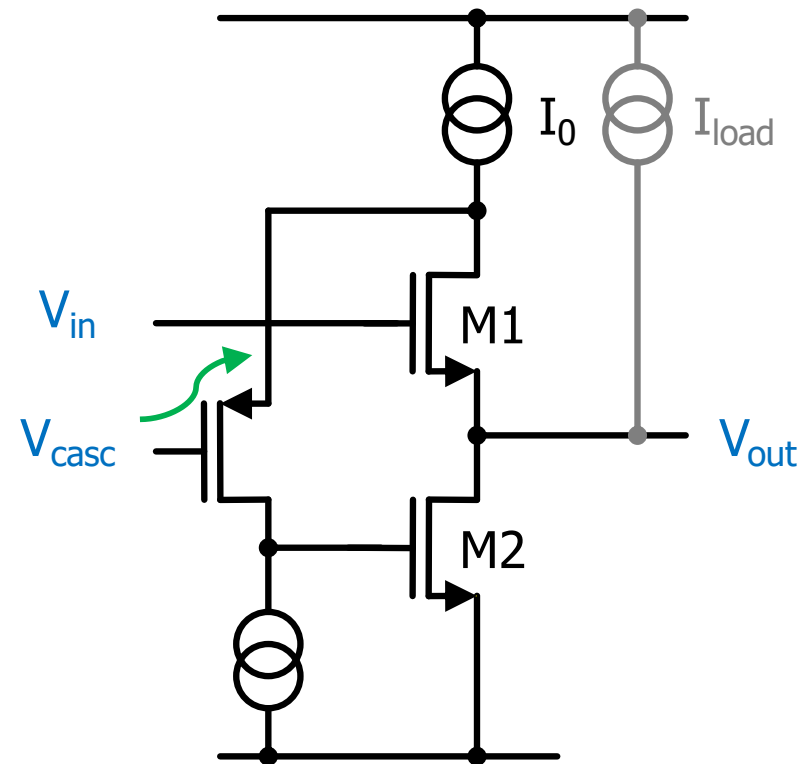
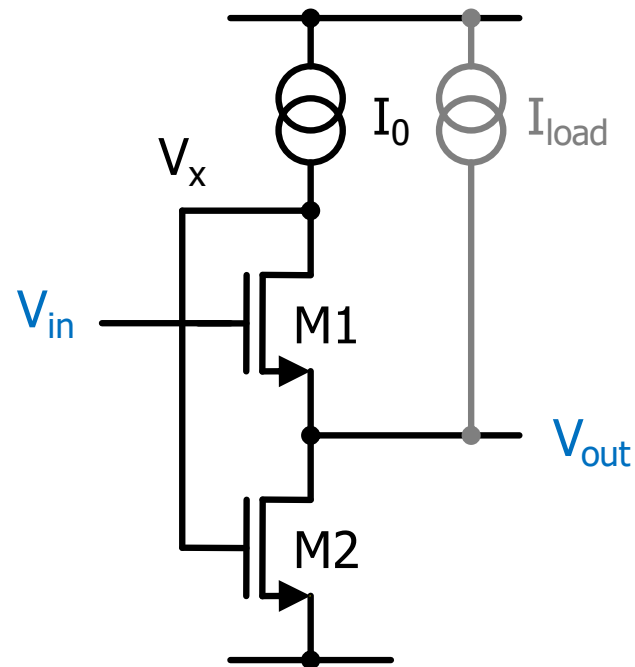
# Simulation of improved version



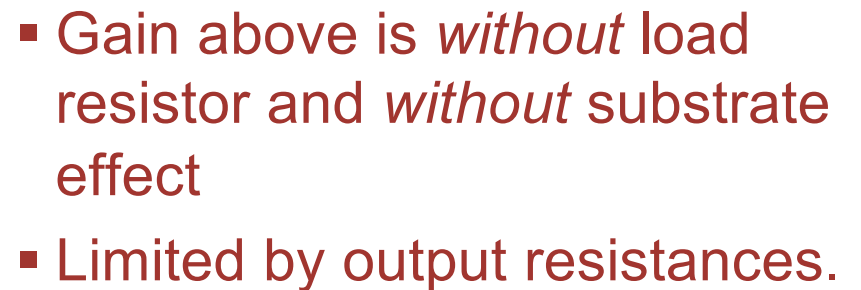
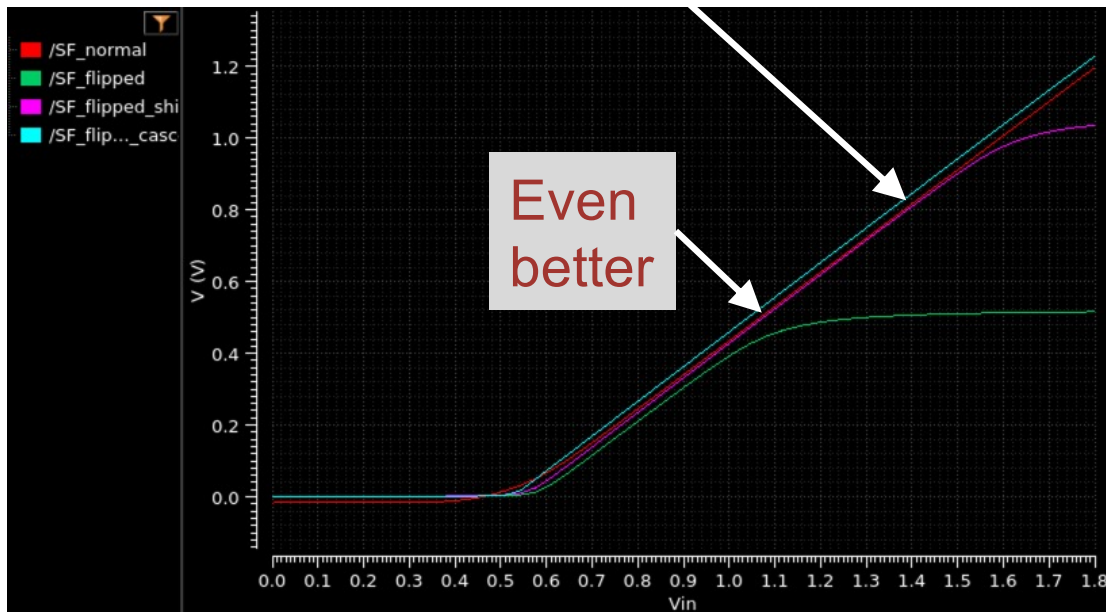


# Improvement – With Cascode

- We can also separate  $V_x$  from the gate of M2 and force  $V_x$  to a voltage with a PMOS cascode
  - Choose  $V_{casc}$  such that  $I_0$  is just saturated for max. dyn. range



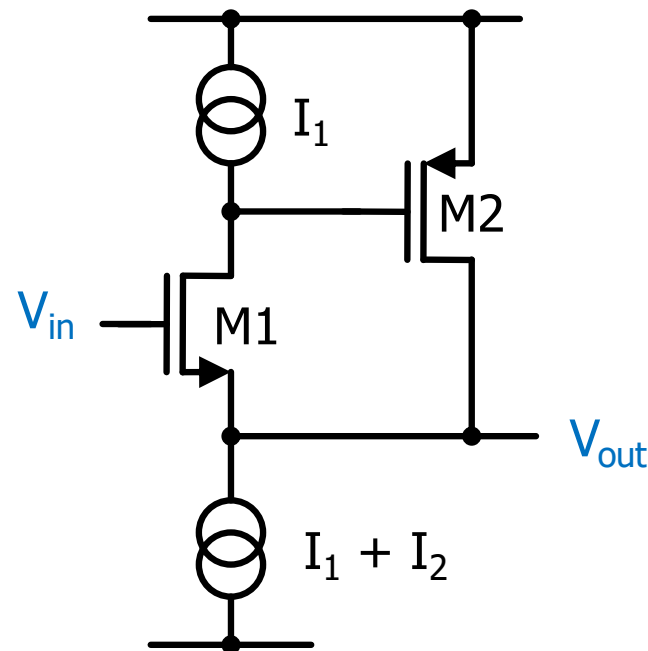
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# 'Super Source Follower'

- The 'Super Source Follower' is another circuit which keeps the current in M1 independent of the load current by providing a second current source (M2) for the load:





# Back to the Normal SF

- For  $V_{BS}=0$ , no  $R_L$ , and a 'good' current source, the gain of the 'normal' SF is limited by the Early effects in M1.

$$\text{gain} = \frac{g_m}{g_{ds} + g_m + \cancel{g_{mb}} + \cancel{g_o}}$$

- The 'problem' is that  $V_{ds}$  of M1 changes with  $V_{out}$
- Can we avoid that ? Yes!  
We 'cascode' the source to a voltage that follows  $V_{out}$ :

